

WHAT IS CLAIMED IS:

1. A method for filling contact holes with metal by two-step deposition of selective tungsten layer:

providing a silicon substrate;

forming a field oxide layer and a junction layer and gate electrode on said silicon substrate;

forming a first insulating layer on the whole structure;

forming first contact holes by removing the desired portion of the first insulating layer to expose said junction layer and gate electrode;

filling first metal layers into the first contact holes, entirely;

forming a conductive layer pattern on the first insulating layer spaced from said first metal layers;

forming a second insulating layer on the whole structure;

forming a second contact hole by removing the desired portion of said second insulating layer to expose both the first metal layer and the conductive layer pattern;

filling a second metal layer into said second contact hole to contact with the first metal layer and conductive layer pattern;

2. The method of claim 1, wherein the first contact hole and the second contact hole are filled with the first metal layer and second metal layer of selective tungsten layer, respectively, by chemical vapor deposition method.